

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









N-Channel Power MOSFET

500V, 5A, 1.38Ω

FEATURES

- 100% UIS and R_g tested
- · Advanced planar process
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS				
PARAMETER	VALUE UNI			
V_{DS}	500	V		
R _{DS(on)} (max)	1.38	Ω		
Q_g	15	nC		

APPLICATIONS

- AC/DC LED Lighting
- Power Supply







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	Limit	UNIT
Drain-Source Voltage		V _{DS}	500	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$		5	
	$T_C = 100$ °C	I _D	2.2	Α
Pulsed Drain Current (Note 2)		I _{DM}	15	А
Total Power Dissipation @ T _C = 25°C		P _{DTOT}	40	W
Single Pulse Avalanche Energy (Note 3)		E _{AS}	122.5	mJ
Single Pulse Avalanche Current (Note 3)		I _{AS}	3.5	А
Operating Junction and Storage Temp	erature Range	T _J , T _{STG}	- 55 to +150	°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	Limit	UNIT	
Junction to Case Thermal Resistance	R _{eJC}	3.1	°C/W	
Junction to Ambient Thermal Resistance	R _{OJA}	62	°C/W	

Thermal Performance Note: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.

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PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	500			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, \ I_D = 250 \mu A$	$V_{GS(TH)}$	2.5	3.3	4.5	V
Gate Body Leakage	$V_{GS} = \pm 30 V$, $V_{DS} = 0 V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 500V, V_{GS} = 0V$	I _{DSS}			1	μΑ
Drain-Source On-State Resistance (Note 4)	$V_{GS} = 10V, I_D = 1.7A$	R _{DS(on)}		1.1	1.38	Ω
Forward Transconductance (Note 4)	$V_{DS} = 10V, I_D = 3.4A$	g _{fs}		2.5		S
Dynamic (Note 5)						
Total Gate Charge	$V_{DS} = 400V, I_D = 3.4A,$	Q_g		15		
Gate-Source Charge		Q_{gs}		4		nC
Gate-Drain Charge	$V_{GS} = 10V$	Q_{gd}		7		
Input Capacitance	$V_{DS} = 50V, V_{GS} = 0V,$	C _{iss}		586		
Output Capacitance		C _{oss}		45		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		1		
Gate Resistance	f = 1.0MHz, open drain	R_g	0.9	3	6	Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 250V, R_G = 5\Omega,$ $I_D = 3.4A, V_{GS} = 10V$	t _{d(on)}		8.2		
Turn-On Rise Time		t _r		20.4		
Turn-Off Delay Time		t _{d(off)}		15.4		ns
Turn-Off Fall Time		t _f		20		
Source-Drain Diode						
Forward Voltage (Note 4)	$I_S = 3.4A, V_{GS} = 0V$	V_{SD}			1.3	V
Reverse Recovery Time	I _S = 3.4A	t _{rr}		205		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q _{rr}		1.5		μC

Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L=20mH, $I_{AS}=3.5A$, $V_{DD}=50V$, $R_{G}=25\Omega$, Starting $T_{J}=25^{\circ}C$
- 4. Pulse test: PW $\leq 300 \mu s$, duty cycle $\leq 2\%$
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.

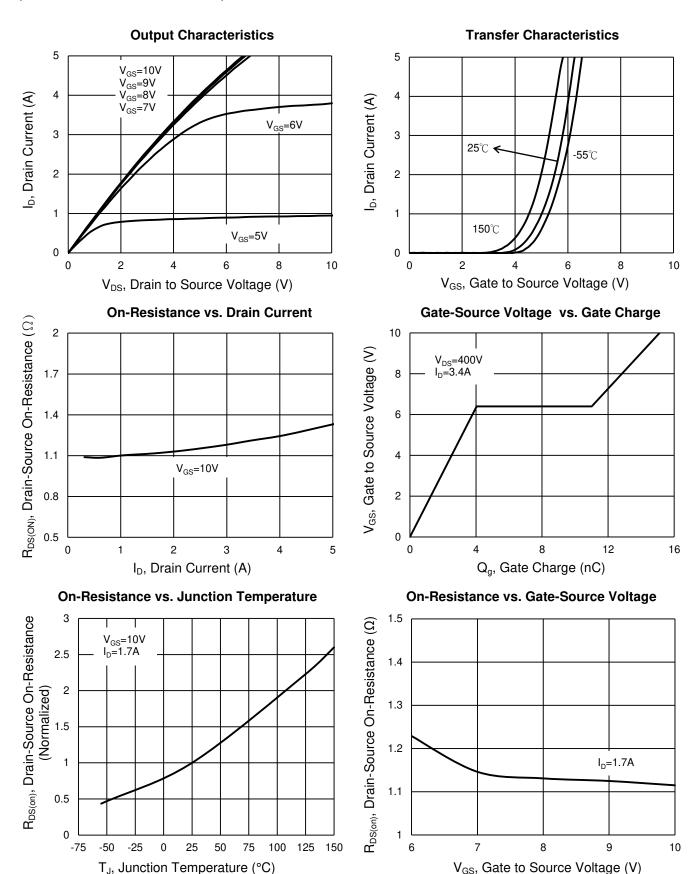
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM5NC50CF C0G	ITO-220S	50pcs / Tube



CHARACTERISTICS CURVES

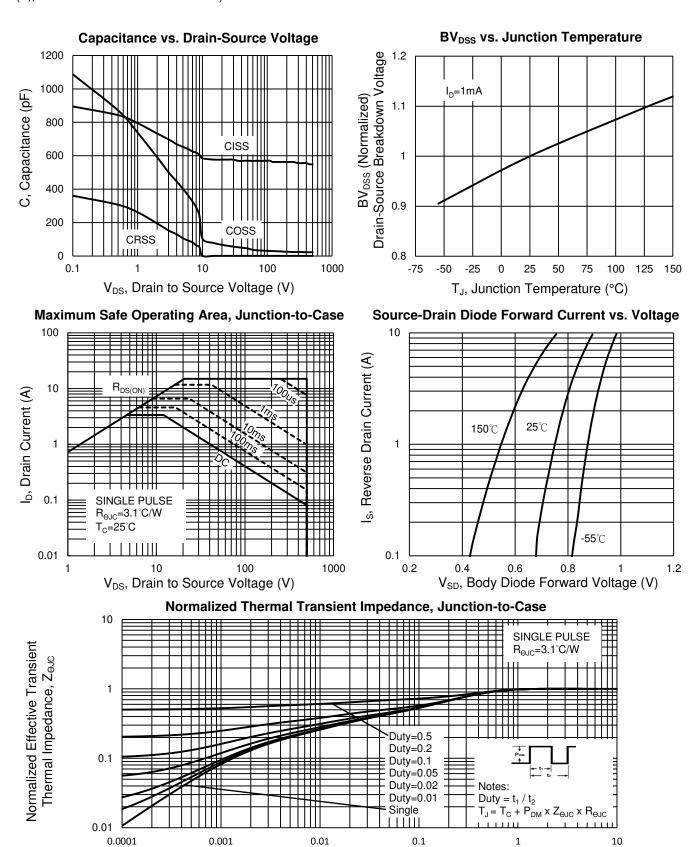
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$





CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

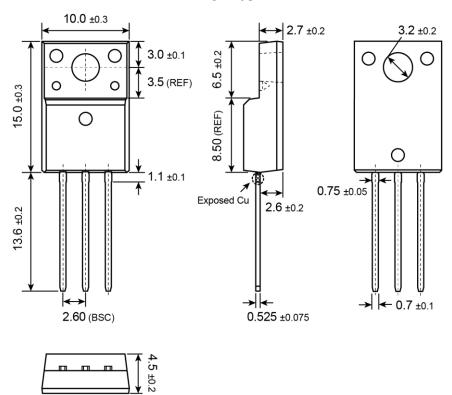


t, Square Wave Pulse Duration (sec)



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

ITO-220S



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MARKING DIAGRAM



G = Halogen Free

Y = Year Code

WW = Week Code (01~52)

F = Factory Code



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